TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

# MT6L03AE

## VHF~UHF Band Low Noise Amplifier Applications

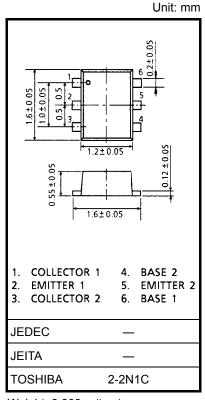
Two devices are built in to the super-thin and extreme super mini (6 pins) package: ES6

#### **Mounted Devices**

	Q1/Q2: SSM (TESM)		
Three-pins (SSM/TESM) mold products are corresponded.	MT3S03AS (MT3S03AT)		

### **Absolute Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Q1/Q2	Unit	
Collector-base voltage	$V_{CBO}$	10	V	
Collector-emitter voltage	V <sub>CEO</sub>	5	V	
Emitter-base voltage	$V_{EBO}$	2	V	
Collector current	IC	40	mA	
Base current	ΙΒ	10	mA	
Collector power dissipation	P <sub>C</sub> (Note 1)	100	mW	
Junction temperature	Tj	125	°C	
Storage temperature range	T <sub>stg</sub>	<b>−55~125</b>	°C	



Weight: 0.003 g (typ.)

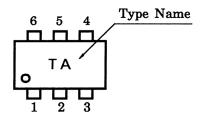
Note: Using continuously under heavy loads (e.g. the application of

high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

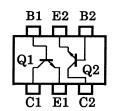
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Total power dissipation of Q1 and Q2.

## Marking



#### Pin Assignment (top view)



## Electrical Characteristics Q1/Q2 (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = 5 \text{ V}, I_E = 0$	_	_	0.1	μА	
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 1 V, I <sub>C</sub> = 0	_	_	1	μА	
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 5 mA	80	_	160		
Transition frequency	f <sub>T</sub> (1)	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 5 mA	5	7	_	GHz	
	f <sub>T</sub> (2)	$V_{CE} = 3 \text{ V}, I_{C} = 10 \text{ mA}$	7	10	_		
Insertion gain	S <sub>21e</sub>   <sup>2</sup> (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	5	_	- dB	
	S <sub>21e</sub>   <sup>2</sup> (2)	$V_{CE} = 3 \text{ V}, I_{C} = 20 \text{ mA}, f = 2 \text{ GHz}$	3	6.5	_		
Noise figure —	NF (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	1.7	3	dB	
	NF (2)	$V_{CE} = 3 \text{ V}, I_{C} = 7 \text{ mA}, f = 2 \text{ GHz}$	_	1.4	2.2		
Reverse transfer capacitance	C <sub>re</sub>	$V_{CB} = 1 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$ (Note 2)	_	0.8	1.15	pF	

Note 2:  $C_{\text{re}}$  is measured by 3 terminal method with capacitance bridge.

## **Handling Precaution**

When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

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20070701-EN GENERAL

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